YJ Planar Schottky Barrier Diode Die Specification

30V 0.1A,13mil, Schottky barrier diode die based on silicon planar process Part No.: PSB013L030AS-155A

Main Products Characterstics

- Average forward current: IF(AV) = 0.1 A
- Maximum operating junction temperature: Tj = 125 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Al/3.5um



Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V _{RRM}	30 V
Average forward current	I _{F(AV)}	0.1 A
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	1 A
Storage temperature range	T _{stg}	-50 to +125 °C
Maximum operating junction temperature	Τ _j	125 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage I _R = 1mA	V_{BR}	30 V	50V
Maximum forward voltage drop $I_F = 0.1A$ Pulse Test: tp = 300 µs, $\delta \leqslant 2\%$	V _F	0.6V	0.5V
Maximum reverse current V_R = 35V Pulse Test: tp = 300 µs, $\delta \leq 2\%$	I _R	5uA	0.4uA

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:	
Yangjie Electronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.	Store in original container, in dessicated nitrogen, with no contamination.	
	Shelf life for parts stored in above condition is 2 years.	
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.	

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Rev.O 2021/07/28